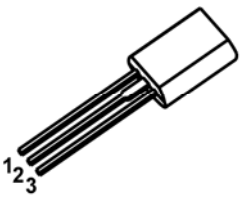
TO-92MOD Plastic-Encapsulate Transistors

2SC2482 TRANSISTOR (NPN)

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



FEATURE

- High Voltage :Vceo=300V
- Small Collector Output Capacitance: Cob=3.0pF(Typ)

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

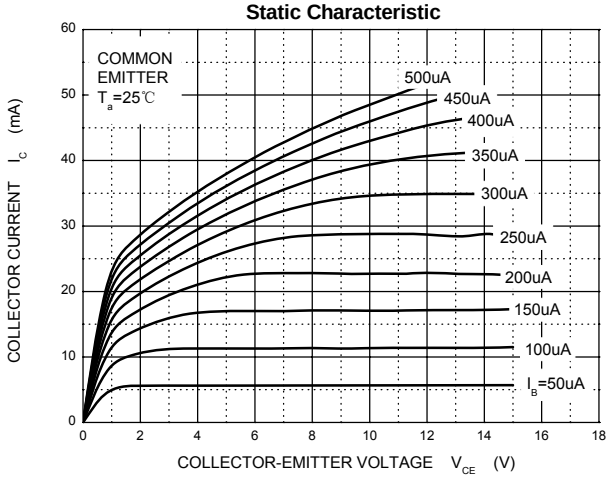
ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= 100μA, I_E=0	300			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 3mA ,I_B=0	300			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA,I_C=0	7			V
Collector cut-off current	I_{CBO}	V_{CB}= 240 V, I_E=0			1.0	μA
Collector cut-off current	I_{CEO}	V_{CB}= 220 V, I_B=0			5.0	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 7V, I_C=0			1.0	μA
DC current gain	h_{FE}	V_{CE}=10V, I_C=20mA	30		150	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= 10mA, I_B=1mA			1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=10mA, I_B=1mA			1.0	V
Transition frequency	f_T	V_{CE}=10V, I_C=20mA,f=30MHz	50			MHz
Collector output capacitance	Cob	V_{CB}=20V, I_E=0, f=1MHz		3		pF

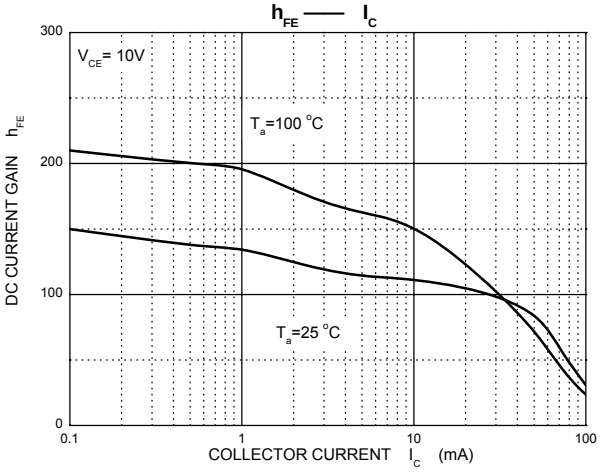
CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	30-90	90-150

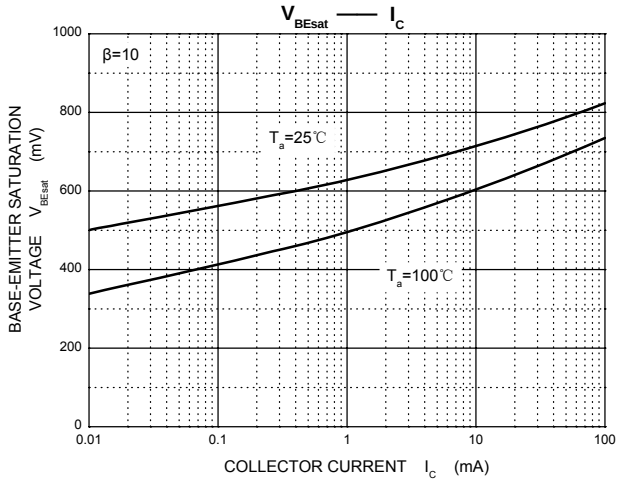
Static Characteristic



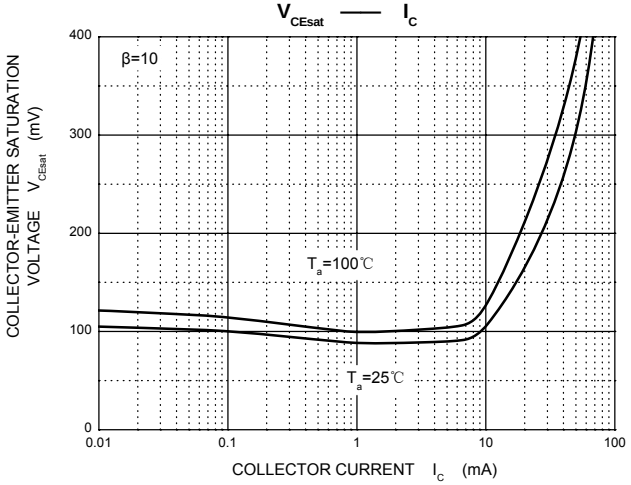
h_{FE} —— I_C



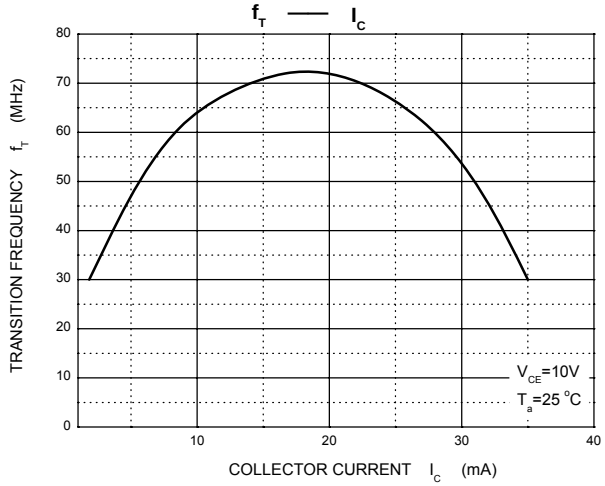
V_{BEsat} —— I_C



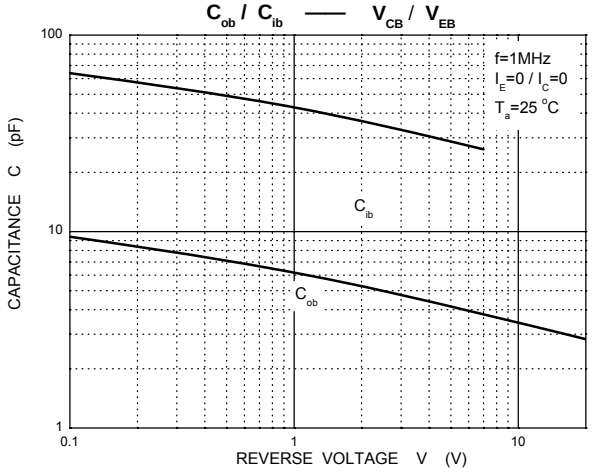
V_{CEsat} —— I_C



f_T —— I_C



C_{ob} / C_{ib} —— V_{CB} / V_{EB}



P_c —— T_a